Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of http://www.nxp.com, http://www.philips.com/ or http://www.semiconductors.philips.com/, use **http://www.nexperia.com**

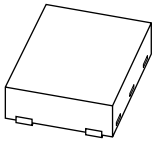
Instead of sales.addresses@www.nxp.com or sales.addresses@www.semiconductors.philips.com, use **salesaddresses@nexperia.com** (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:
- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved
Should be replaced with:
- **© Nexperia B.V. (year). All rights reserved**.

If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia



PBSS5620PA

20 V, 6 A PNP low V_{CEsat} (BISS) transistor

Rev. 01 — 13 April 2010 Product data sheet

1. Product profile

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

NPN complement: PBSS4620PA.

1.2 Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability

1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

1.4 Quick reference data

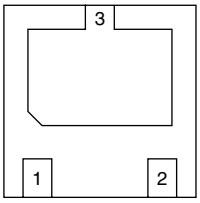
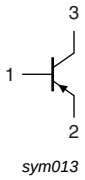
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	–20	V
I_C	collector current			-	-	–6	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms		-	-	–7	A
R_{CEsat}	collector-emitter saturation resistance	I_C = –6 A; I_B = –300 mA	[1]	-	39	58	mΩ

[1] Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$.

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter		
3	collector		

Transparent top view

sym013

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS5620PA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; three terminals; body 2 × 2 × 0.65 mm	SOT1061

4. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5620PA	AA

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	−20	V
V_{CEO}	collector-emitter voltage	open base		-	−20	V
V_{EBO}	emitter-base voltage	open collector		-	−7	V
I_C	collector current			-	−6	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms		-	−7	A
I_B	base current			-	−600	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	500	mW
			[2]	-	1	W
			[3]	-	1.4	W
			[4]	-	2.1	W

Table 5. Limiting values *...continued*

In accordance with the Absolute Maximum Rating System (IEC 60134).

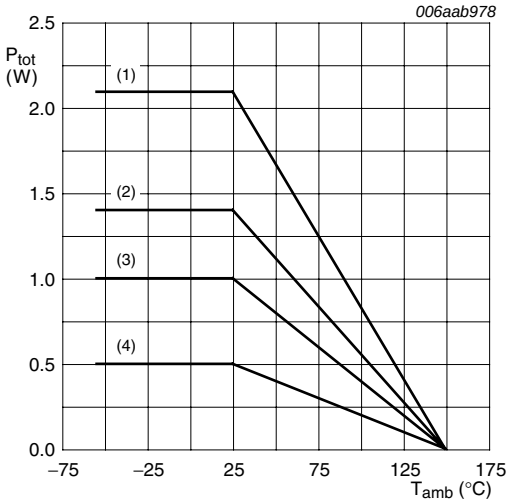
Symbol	Parameter	Conditions	Min	Max	Unit
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		−55	+150	°C
T_{stg}	storage temperature		−65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm^2.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm^2.

[4] Device mounted on a ceramic PCB, Al_2O_3, standard footprint.



(1) Ceramic PCB, Al_2O_3, standard footprint

(2) FR4 PCB, mounting pad for collector 6 cm^2

(3) FR4 PCB, mounting pad for collector 1 cm^2

(4) FR4 PCB, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

Table 6. Thermal characteristics

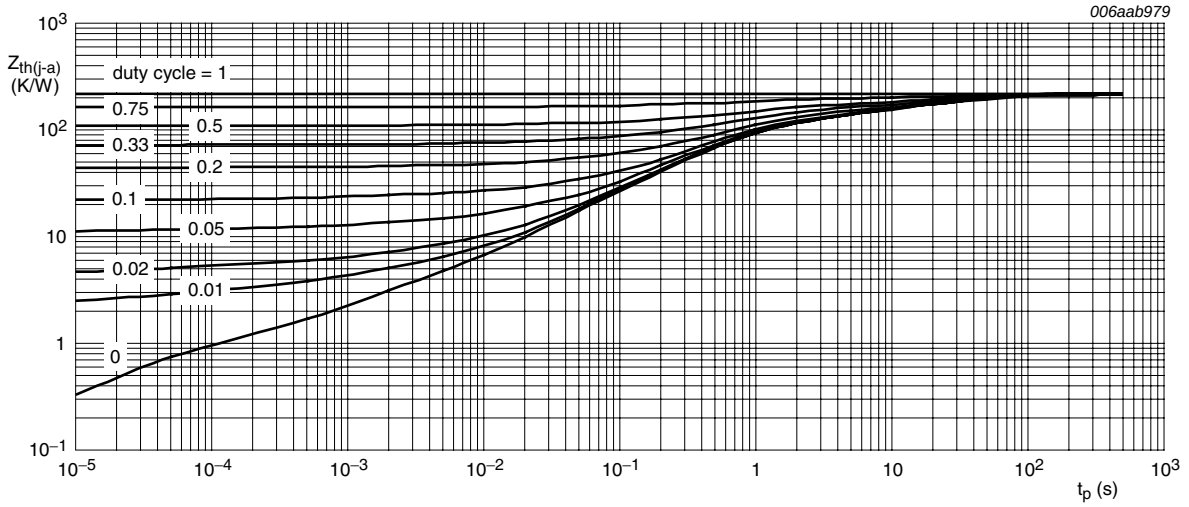
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W
			[2]	-	-	125	K/W
			[3]	-	-	90	K/W
			[4]	-	-	60	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm^2.

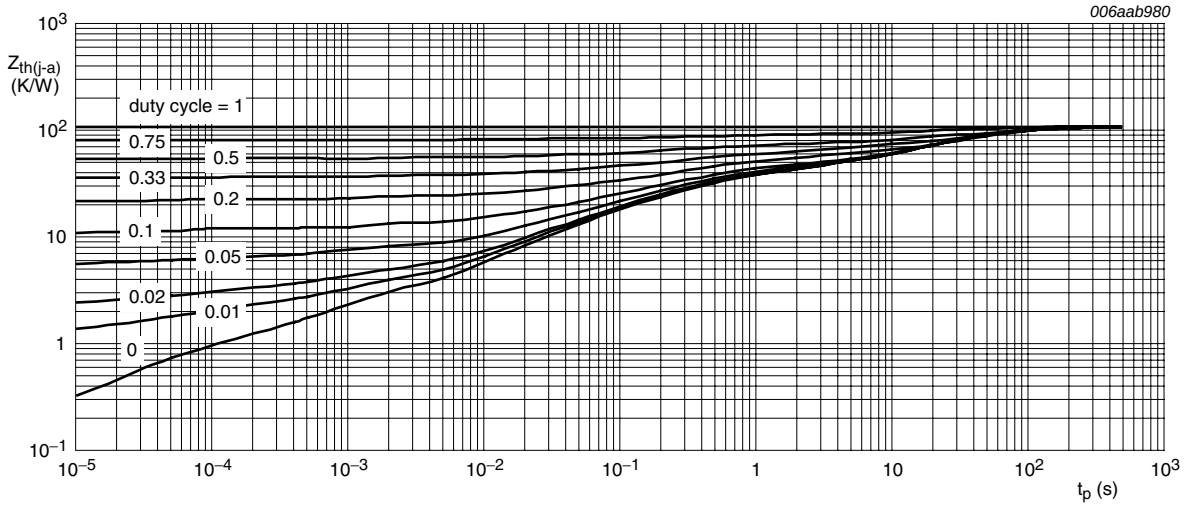
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm^2.

[4] Device mounted on a ceramic PCB, Al_2O_3, standard footprint.



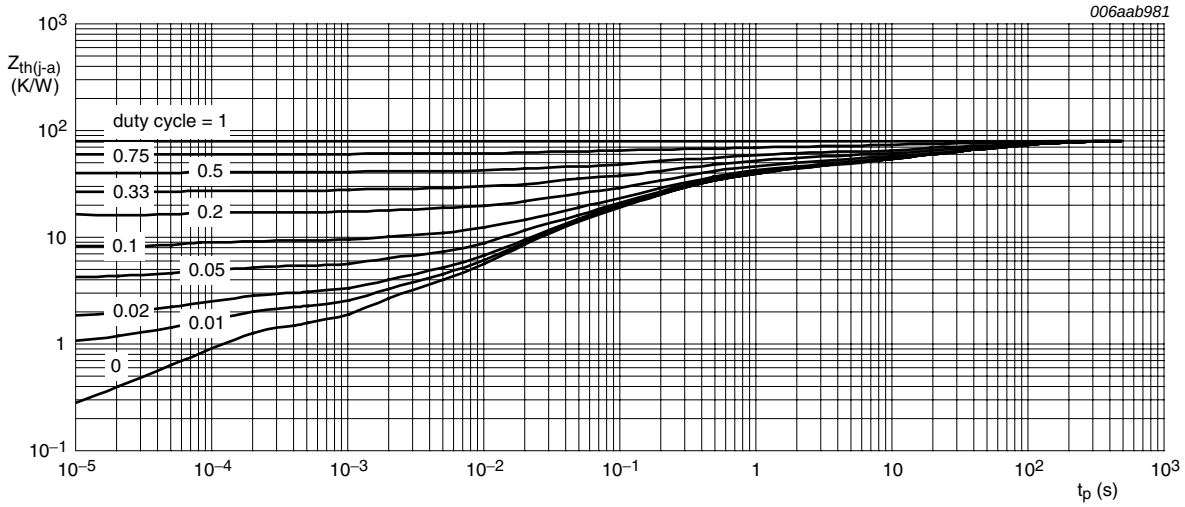
FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



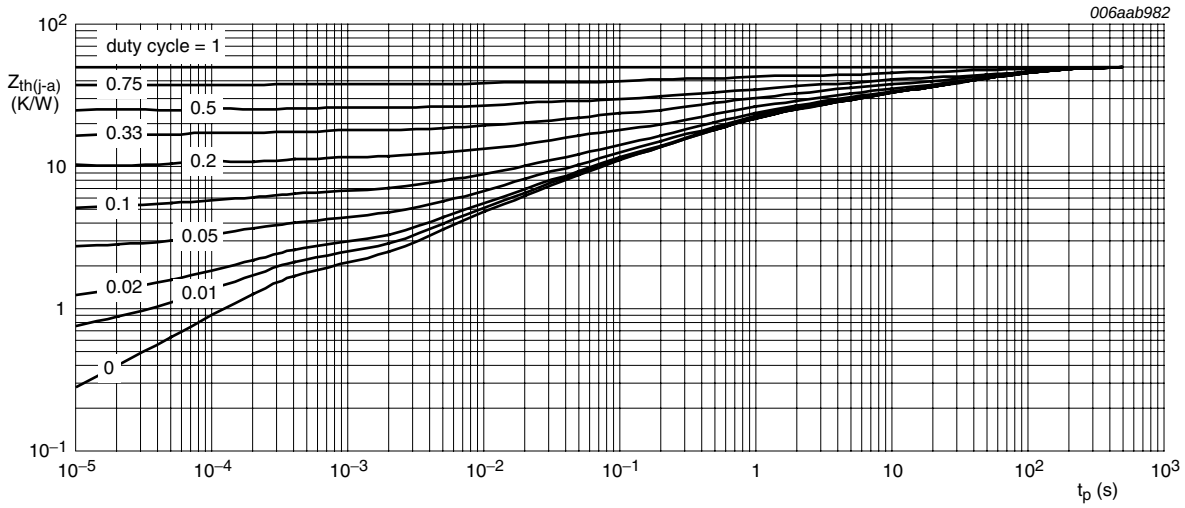
FR4 PCB, mounting pad for collector 1 cm^2

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 6 cm^2

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al_2O_3, standard footprint

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

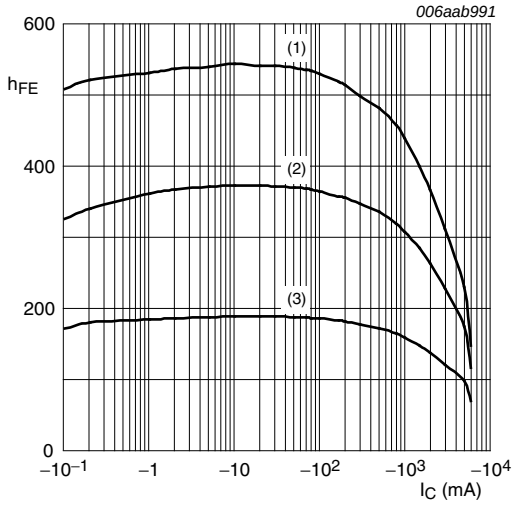
7. Characteristics

Table 7. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	V_{CB} = –16 V; I_E = 0 A		-	-	–100	nA
		V_{CB} = –16 V; I_E = 0 A; T_j = 150 °C		-	-	–50	μA
I_{CES}	collector-emitter cut-off current	V_{CE} = –16 V; V_{BE} = 0 V		-	-	–100	nA
I_{EBO}	emitter-base cut-off current	V_{EB} = –5 V; I_C = 0 A		-	-	–100	nA
h_{FE}	DC current gain	V_{CE} = –2 V	[1]				
		I_C = –0.5 A		230	345	-	
		I_C = –1 A		220	320	-	
		I_C = –2 A		190	275	-	
		I_C = –6 A		110	155	-	
V_{CEsat}	collector-emitter saturation voltage	I_C = –0.5 A; I_B = –50 mA	[1]	-	–25	–40	mV
		I_C = –1 A; I_B = –50 mA	[1]	-	–50	–80	mV
		I_C = –1 A; I_B = –10 mA	[1]	-	–80	–130	mV
		I_C = –2 A; I_B = –20 mA	[1]	-	–135	–210	mV
		I_C = –3 A; I_B = –30 mA	[1]	-	–215	–325	mV
		I_C = –4 A; I_B = –400 mA	[1]	-	–150	–230	mV
		I_C = –6 A; I_B = –300 mA	[1]	-	–235	–350	mV
R_{CEsat}	collector-emitter saturation resistance	I_C = –6 A; I_B = –300 mA	[1]	-	39	58	mΩ
V_{BEsat}	base-emitter saturation voltage	I_C = –1 A; I_B = –10 mA	[1]	-	–0.75	–0.9	V
		I_C = –6 A; I_B = –300 mA	[1]	-	–1.03	–1.1	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = –2 V; I_C = –2 A	[1]	-	–0.76	–0.9	V
t_d	delay time	V_{CC} = –9 V; I_C = –2 A; I_{Bon} = –0.1 A; I_{Boff} = 0.1 A		-	19	-	ns
t_r	rise time			-	59	-	ns
t_{on}	turn-on time			-	78	-	ns
t_s	storage time			-	265	-	ns
t_f	fall time			-	55	-	ns
t_{off}	turn-off time			-	320	-	ns
f_T	transition frequency	V_{CE} = –10 V; I_C = –100 mA; f = 100 MHz		50	80	-	MHz
C_c	collector capacitance	V_{CB} = –10 V; I_E = i_e = 0 A; f = 1 MHz		-	75	90	pF

[1] Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$.



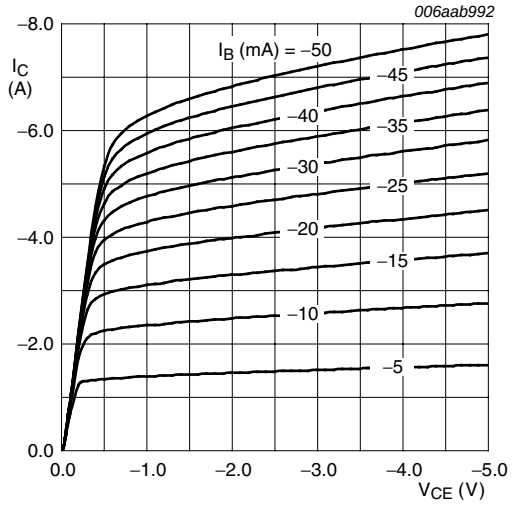
V_{CE} = −2 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

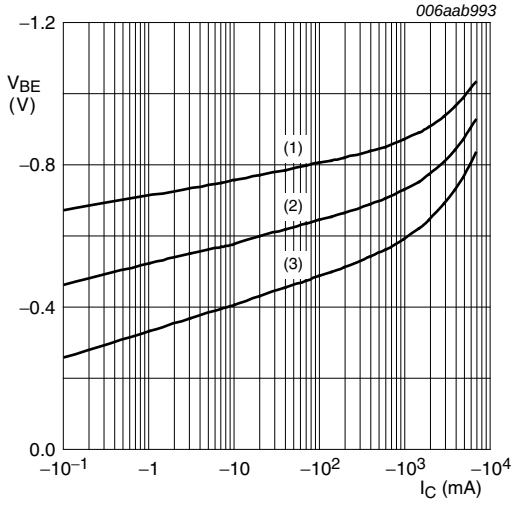
(3) T_{amb} = −55 °C

Fig 6. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig 7. Collector current as a function of collector-emitter voltage; typical values



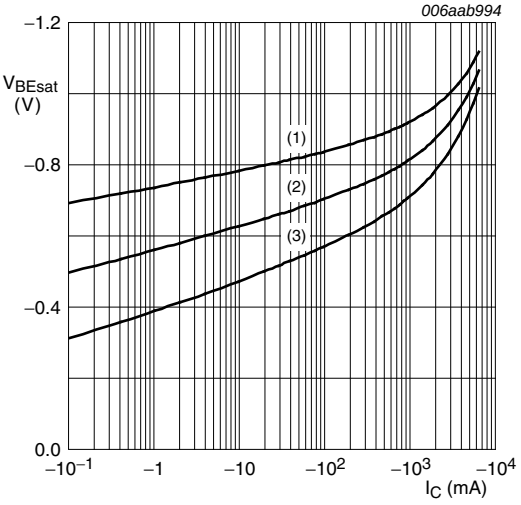
V_{CE} = −2 V

(1) T_{amb} = −55 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 8. Base-emitter voltage as a function of collector current; typical values



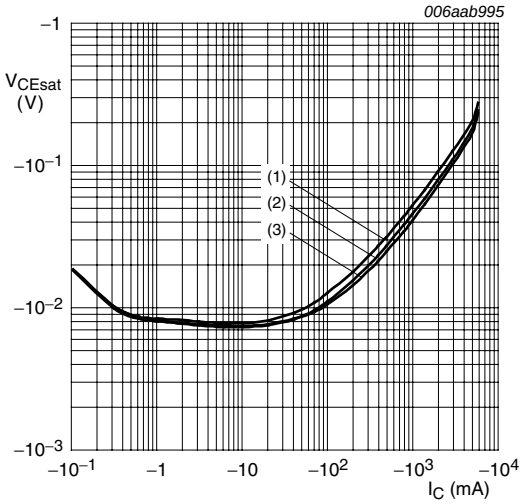
I_C/I_B = 20

(1) T_{amb} = −55 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 9. Base-emitter saturation voltage as a function of collector current; typical values



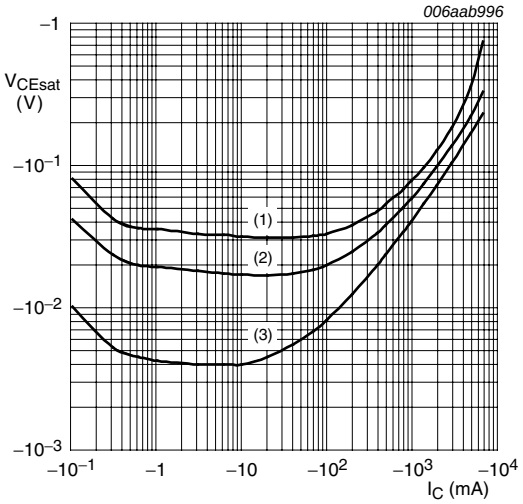
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −55 °C

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values



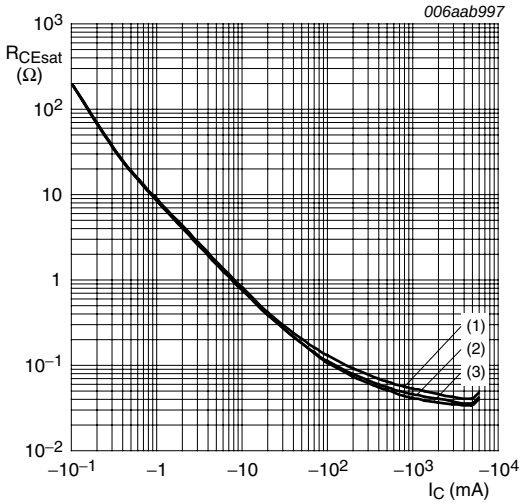
T_{amb} = 25 °C

(1) I_C/I_B = 100

(2) I_C/I_B = 50

(3) I_C/I_B = 10

Fig 11. Collector-emitter saturation voltage as a function of collector current; typical values



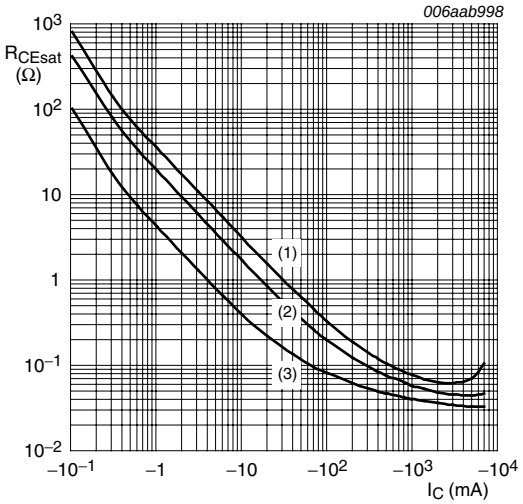
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −55 °C

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values



T_{amb} = 25 °C

(1) I_C/I_B = 100

(2) I_C/I_B = 50

(3) I_C/I_B = 10

Fig 13. Collector-emitter saturation resistance as a function of collector current; typical values

8. Test information

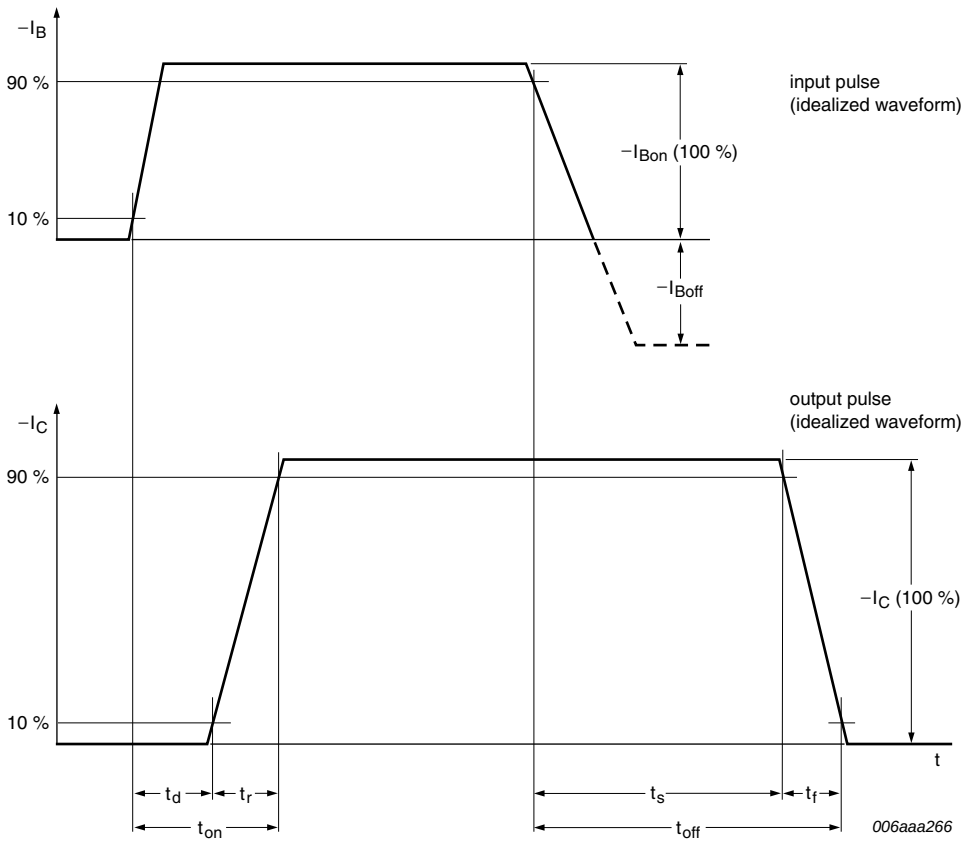
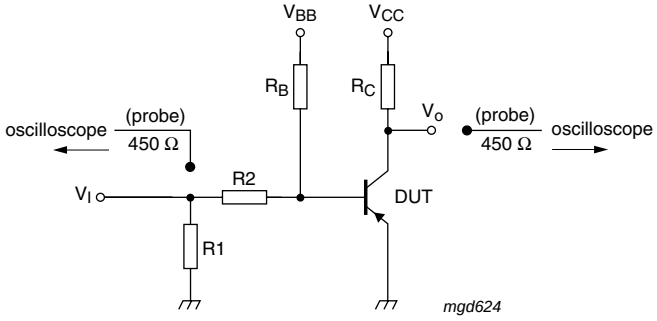


Fig 14. BISS transistor switching time definition



V_{CC} = −9 V; I_C = −2 A; I_{Bon} = −0.1 A; I_{Boff} = 0.1 A

Fig 15. Test circuit for switching times

9. Package outline

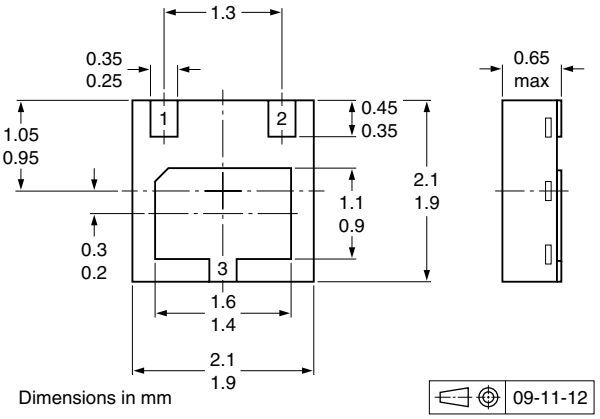


Fig 16. Package outline SOT1061 (HUSON3)

10. Packing information

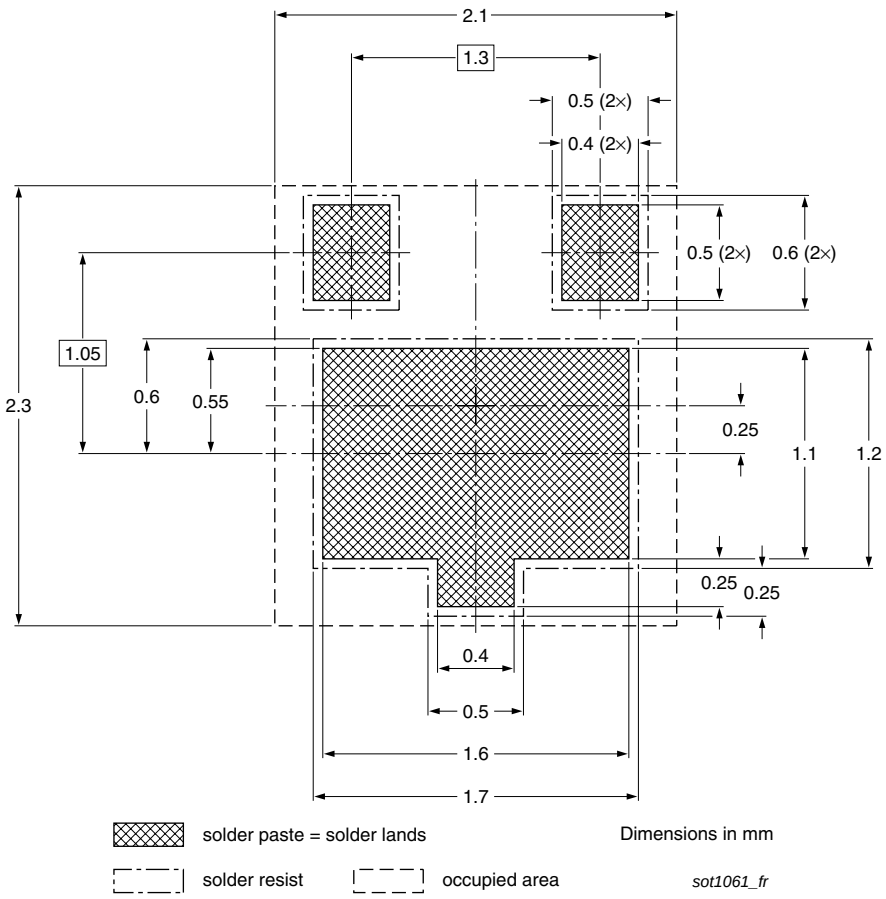
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			3000
PBSS5620PA	SOT1061	4 mm pitch, 8 mm tape and reel	-115

[1] For further information and the availability of packing methods, see Section 14.

11. Soldering



Reflow soldering is the only recommended soldering method.

Fig 17. Reflow soldering footprint SOT1061 (HUSON3)

12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5620PA_1	20100413	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

13.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

13.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on a weakness or default in the customer application/use or the application/use of customer's third party customer(s) (hereinafter both referred to as "Application"). It is customer's sole responsibility to check whether the NXP Semiconductors product is suitable and fit for the Application planned. Customer has to do all necessary testing for the Application in order to avoid a default of the Application and the product. NXP Semiconductors does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Non-automotive qualified products — Unless this data sheet expressly states that this specific NXP Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. NXP Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without NXP Semiconductors' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond NXP Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies NXP Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond NXP Semiconductors' standard warranty and NXP Semiconductors' product specifications.

13.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

14. Contact information

For more information, please visit: **http://www.nxp.com**

For sales office addresses, please send an email to: **salesaddresses@nxp.com**

15. Contents

For more information, please visit: http://www.nxp.com
For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 13 April 2010
Document identifier: PBSS5620PA_1

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT ***category:***

Click to view products by Nexperia ***manufacturer:***

Other Similar products are found below :

619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE158 NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SD2150T100R SP000011176 FMMTA92QTA 2N2369ADCSM 2N5769 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E US6T6TR NJL0281DG 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E IMZ2AT108 UMX21NTR MCH6102-TL-E NJL0302DG 2N3583 2SA1434-TB-E 2SC3143-4-TB-E 2SD1621S-TD-E NTE103 30A02MH-TL-E NSV40301MZ4T1G NTE101 NTE13 NTE15 NTE16001